



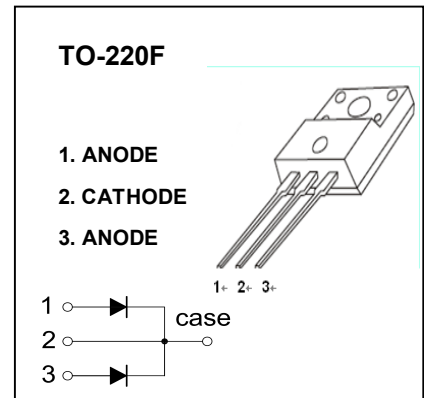
## TO-220F Plastic-Encapsulate Diodes

### SBL3030, 35, 40, 45, 50FCT

SCHOTTKY BARRIER RECTIFIER

#### FEATURES

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications



#### MAXIMUM RATINGS ( $T_a=25^{\circ}\text{C}$ unless otherwise noted )

Symbol	Parameter	Value					Unit
		SBL30 30FCT	SBL30 35FCT	SBL30 40FCT	SBL30 45FCT	SBL30 50FCT	
$V_{RRM}$	Peak repetitive reverse voltage	30	35	40	45	50	V
$V_{RWM}$	Working peak reverse voltage						
$V_R$	DC blocking voltage						
$V_{R(RMS)}$	RMS reverse voltage	21	24.5	28	31.5	35	V
$I_O$	Average rectified output current	30					A
$I_{FSM}$	Non-Repetitive peak forward surge current 8.3ms half sine wave	250					A
$P_D$	Power dissipation	2					W
$R_{\theta JA}$	Thermal resistance from junction to ambient	50					$^{\circ}\text{C}/\text{W}$
$T_j$	Junction temperature	125					$^{\circ}\text{C}$
$T_{stg}$	Storage temperature	-55~+150					$^{\circ}\text{C}$

**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Device	Test conditions	Min	Typ	Max	Unit
Reverse voltage	V <sub>(BR)</sub>	SBL3030FCT	I <sub>R</sub> =1mA	30			V
		SBL3035FCT		35			
		SBL3040FCT		40			
		SBL3045FCT		45			
		SBL3050FCT		50			
Reverse current	I <sub>R</sub>	SBL3030FCT	V <sub>R</sub> =30V			1	mA
		SBL3035FCT	V <sub>R</sub> =35V				
		SBL3040FCT	V <sub>R</sub> =40V				
		SBL3045FCT	V <sub>R</sub> =45V				
		SBL3050FCT	V <sub>R</sub> =50V				
Forward voltage	V <sub>F</sub>	SBL3030FCT-3045FCT	I <sub>F</sub> =15A			0.55	V
		SBL3050FCT				0.7	
Typical total capacitance	C <sub>tot</sub>	SBL3030FCT-3050FCT	V <sub>R</sub> =4V,f=1MHz		420		pF